



#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	Rds(on)	I <sub>D</sub> T <sub>A</sub> = +25°C
001/	2Ω @ V <sub>GS</sub> = 4V	400mA
60V	2.5Ω @ V <sub>GS</sub> = 2.5V	350mA

### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN62D1LFDQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Backlighting
- Power-management functions
- DC-DC converters

### **Mechanical Data**

- Package: U-DFN1212-3
- Package Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)

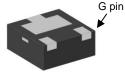
#### U-DFN1212-3 (Type C)



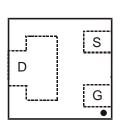




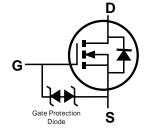
Top View



Bottom View



Pinout Top View



Equivalent Circuit

# **Ordering Information** (Note 4)

Orderable Part Number	Paakaga	Packing			
Orderable Part Number	Package	Qty.	Carrier		
DMN62D1LFDQ-7	U-DFN1212-3 (Type C)	3,000	Tape & Reel		
DMN62D1LFDQ-13	U-DFN1212-3 (Type C)	10,000	Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# Marking Information



K64 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: M = 2025) M = Month (ex: 9 = September)

### Date Code Key

Year	2018	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	F	-	М	Ν	Р	R	S	Т	U	٧	W	Χ
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		VDSS	60	V
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4V	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lo	400 310	mA
Pulsed Drain Current (Note 6)	_	I <sub>DM</sub>	1	A

# **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	0.5	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>ÐJA</sub>	237	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

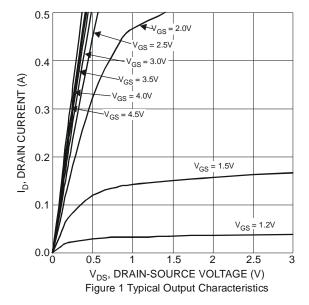
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
		_	_	±100	nA	$V_{GS} = \pm 5V$ , $V_{DS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±500	nA	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$	
		_	_	±2	μΑ	$V_{GS} = \pm 15V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	0.6	—	1	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
		1	0.8	2		V <sub>G</sub> S = 4V, I <sub>D</sub> = 100mA	
Static Drain-Source On-Resistance	Dagger	1	1	2.5	Ω	Vgs = 2.5V, ID = 50mA	
Static Dialii-Source Oil-Resistance	RDS(ON)	-	1.4	3		V <sub>G</sub> S = 1.8V, I <sub>D</sub> = 50mA	
		_	1.8	_		V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 10mA	
Forward Transfer Admittance	Y <sub>fs</sub>	_	1.8	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 200mA	
Diode Forward Voltage	VsD	_	0.8	1.3	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 115mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	1	36	_		.,, , , , , , , , , , , , , , , , ,	
Output Capacitance	Coss	1	4.6	_	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz	
Reverse Transfer Capacitance	Crss	_	3.6	_		1 – 1101112	
Gate Resistance	$R_g$	_	59.8	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	0.55	_			
Gate-Source Charge	Qgs	_	0.08	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250mA$	
Gate-Drain Charge	Qgd	_	0.12	_		ID = 250IIIA	
Turn-On Delay Time	tD(ON)	_	2.1	_	ns		
Turn-On Rise Time	tR	_	2.8	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$	
Turn-Off Delay Time	tD(OFF)	_	21	_	ns	$R_L = 150\Omega$ , $R_G = 25\Omega$ , $R_D = 200$ mA	
Turn-Off Fall Time	tF	_	13.9	_	ns	- ID - 20011IA	

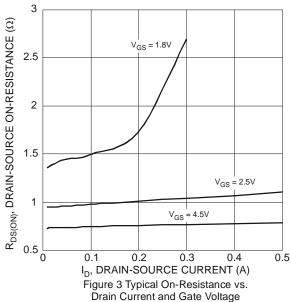
Notes:

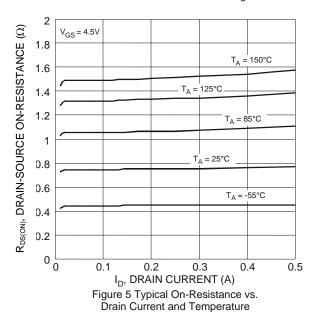
- 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- 6. Repetitive rating, pulse width limited by junction temperature.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.

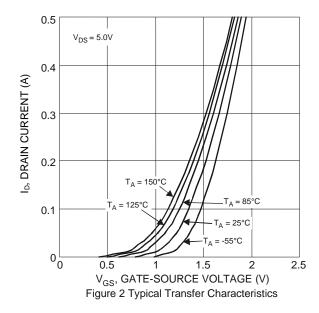


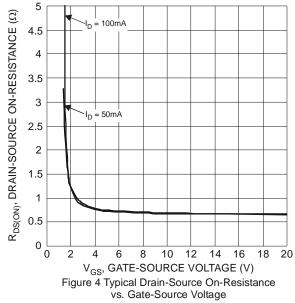












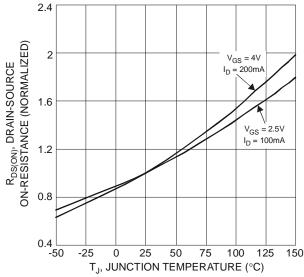
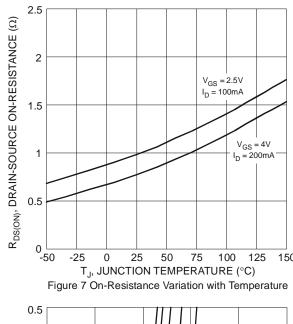
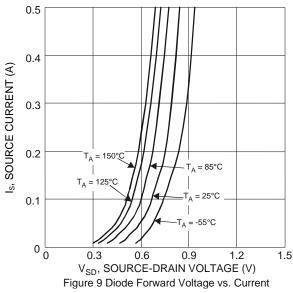


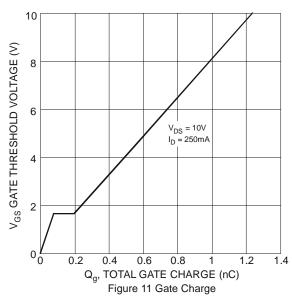
Figure 6 On-Resistance Variation with Temperature

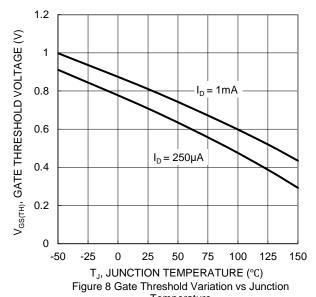


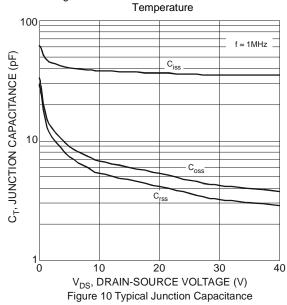


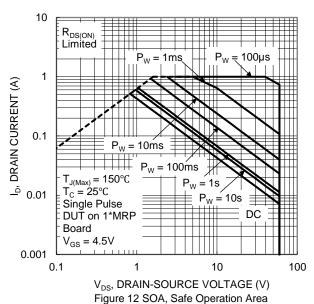




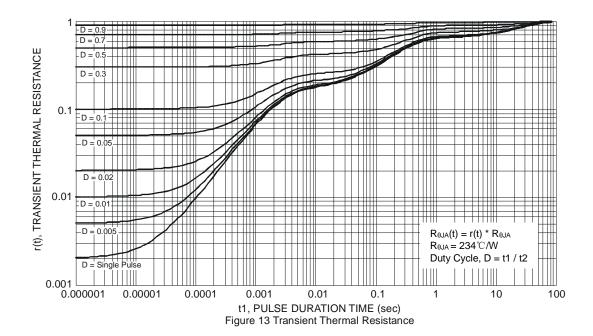










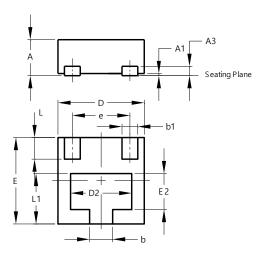




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN1212-3 (Type C)

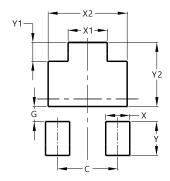


U-DFN1212-3 Type C						
Dim	Min	Max	Тур			
Α	0.47	0.53	0.50			
A1	0	0.05	0.02			
A3	-	-	0.13			
b	0.27	0.37	0.32			
b1	0.17	0.27	0.22			
D	1.15	1.25	1.20			
D2	0.75	0.95	0.85			
е	1	1	0.80			
Ε	1.15	1.25	1.20			
E2	0.40	0.60	0.50			
L	0.25	0.35	0.30			
L1	0.65	0.75	0.70			
All	Dimens	sions in	mm			

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN1212-3 (Type C)



Dimensions	Value (in mm)
С	0.800
G	0.200
Х	0.320
X1	0.520
X2	1.050
Υ	0.450
Y1	0.250
Y2	0.850



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